

FEATURES

- High Output Power: $P_{1dB} = 44.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 38\%$ (Typ.)
- Low $IM_3 = -46\text{dBc}$ @ $P_o = 33.5\text{dBm}$
- Broad Band: 6.4 ~ 7.2GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package

DESCRIPTION

The FLM6472-25F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ\text{C}$	93.7	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

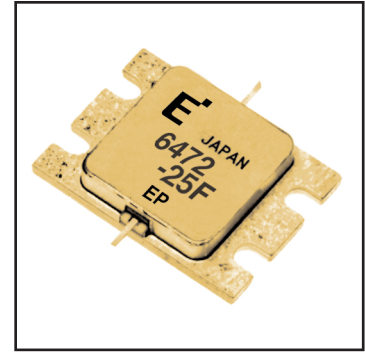
1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 64.0 and -11.2 mA respectively with gate resistance of 25 Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$)

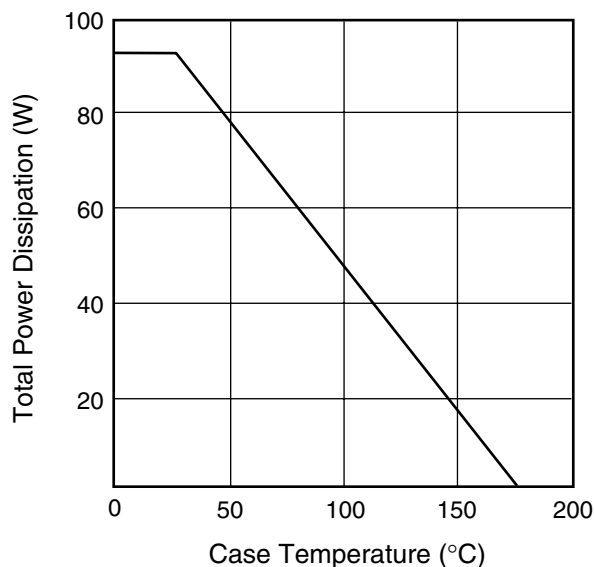
Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	10	15	A
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 6500\text{mA}$	-	10	-	S
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 500\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -500\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.65 I_{DSS}$ (Typ.), $f = 6.4 \sim 7.2 \text{ GHz},$ $Z_S = Z_L = 50 \text{ ohm}$	43.5	44.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		8.5	9.5	-	dB
Drain Current	I_{dsr}		-	6500	7600	mA
Power-added Efficiency	η_{add}		-	38	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 7.2 \text{ GHz}, \Delta f = 10 \text{ MHz}$ 2-Tone Test $P_{out} = 33.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	1.4	1.6	$^\circ\text{C/W}$
Channel Temperature Rise	ΔT_{ch}	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	100	$^\circ\text{C}$

CASE STYLE: IK

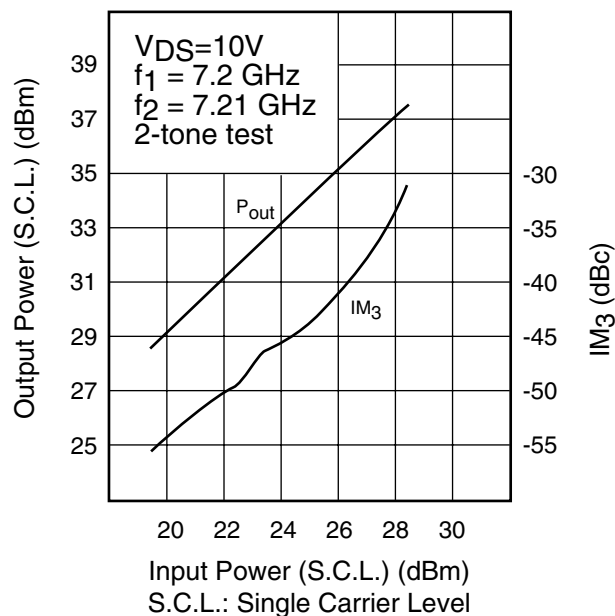
G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level



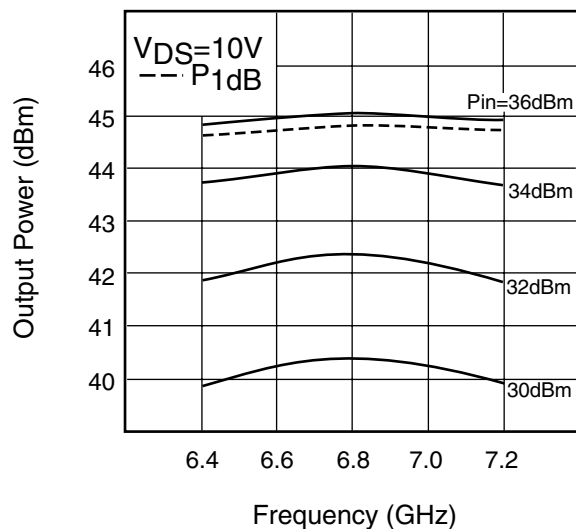
POWER DERATING CURVE



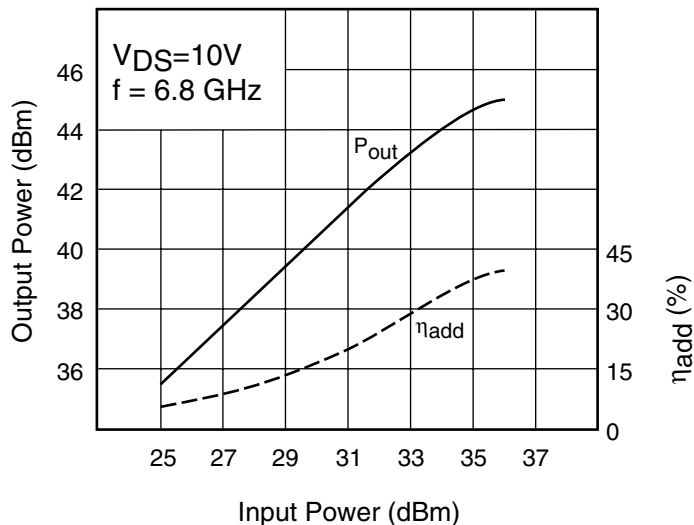
OUTPUT POWER & IM₃ vs. INPUT POWER

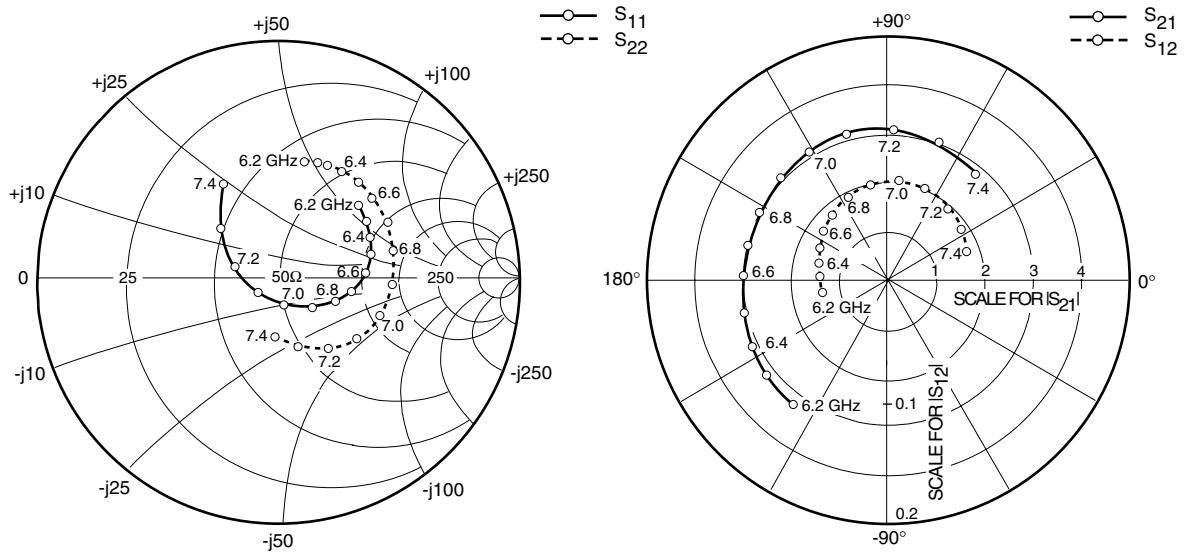


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 6500mA$

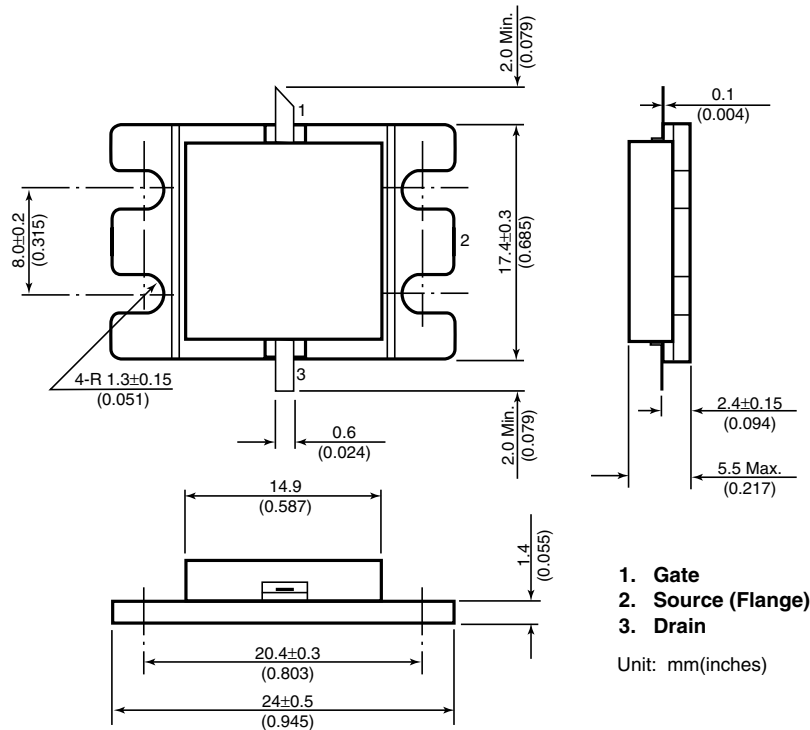
FREQUENCY (MHZ)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6200	.456	42.1	3.198	-129.2	.057	-169.6	.510	71.7
6300	.444	33.6	3.139	-143.1	.058	179.0	.512	66.4
6400	.426	24.4	3.089	-154.7	.061	167.8	.512	59.8
6500	.397	15.3	3.018	-167.8	.064	156.1	.513	51.4
6600	.358	4.4	3.044	178.4	.069	144.0	.512	41.3
6700	.312	-6.6	3.038	165.6	.071	131.3	.502	28.9
6800	.254	-21.0	3.063	151.7	.076	117.2	.488	14.6
6900	.183	-40.2	3.101	136.9	.079	101.6	.466	-1.8
7000	.114	-77.1	3.148	121.1	.081	84.6	.437	-19.7
7100	.104	-149.7	3.164	105.9	.082	68.7	.401	-37.0
7200	.195	164.3	3.139	88.1	.076	53.1	.354	-55.3
7300	.325	138.9	3.042	69.6	.073	32.7	.298	-74.2
7400	.454	120.5	2.871	50.6	.069	19.4	.238	-93.9

FLM6472-25F

C-Band Internally Matched FET

Case Style "IK"

Metal-Ceramic Hermetic Package



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CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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